

CLAIM AMENDMENTS

13. (Currently Amended) A monolithic microwave integrated circuit (MMIC) comprising:

a transistor having an input terminal and an insulating film around the transistor, affecting input capacitance of the transistor, the input capacitance changing directly with thickness of the insulating film;

an input line connected to the input terminal;~~and~~

a metal-insulator-metal (MIM) capacitor, including two metal electrodes separated by part of the insulating film, one of the metal electrodes of the MIM capacitor being connected to the input terminal of the transistor; and

an open stub capacitance connected to the input line, remote from the input terminal of the transistor and including part of the insulating film as a dielectric, capacitance ~~capacitance~~ capacitances of the MIM capacitor and the open stub capacitance changing inversely with the thickness of the insulating film, whereby variations in the input capacitance of the transistor and the ~~capacitance~~ capacitances of the MIM capacitor and the open stub capacitance due to variations in the thickness of the insulating film are compensated.

14. (Previously Added) The MMIC according to claim 13 including a bias circuit connected in parallel with the MIM capacitor.

15. (Currently Amended) A monolithic microwave integrated circuit (MMIC) comprising:

a transistor having an output terminal and an insulating film around the transistor, affecting output capacitance of the transistor, the output capacitance changing directly with thickness of the insulating film;

an output line connected to the output terminal;~~and~~

a metal-insulator-metal (MIM) capacitor, including two metal electrodes separated by part of the insulating film, one of the metal electrodes of the MIM capacitor being connected to the output terminal of the transistor; and

an open stub capacitance connected to the output line, remote from the output terminal of the transistor and including part of the insulating film as a dielectric, capacitance ~~capacitance~~ capacitances of the MIM capacitor and the open stub capacitance changing inversely with the thickness of the insulating film, whereby variations in the output capacitance of the

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transistor and the ~~capacitance~~ capacitances of the MIM capacitor and the open stub capacitance due to variations in the thickness of the insulating film are compensated.

16. (Previously Added) The MMIC according to claim 14 including a bias circuit connected in parallel with the MIM capacitor.
